

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
12 December 2002 (12.12.2002)

PCT

(10) International Publication Number
WO 02/099875 A1

(51) International Patent Classification⁷: **H01L 21/8242**

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(21) International Application Number: **PCT/EP02/06090**

(22) International Filing Date: 3 June 2002 (03.06.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
01113838.5 6 June 2001 (06.06.2001) EP

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(81) Designated States (*national*): JP, KR, SG, US.

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Published:

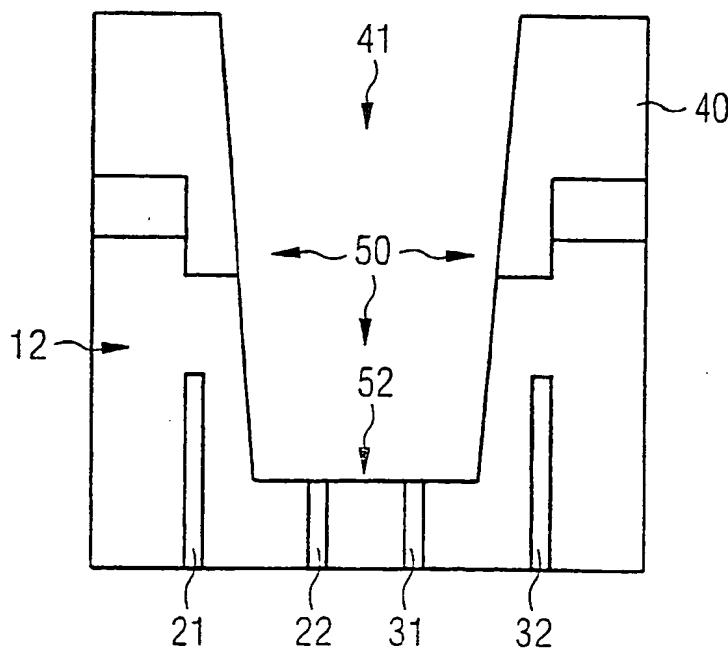
— with international search report

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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD FOR MANUFACTURING A TRENCH CAPACITOR WITH AN ISOLATION TRENCH



(57) Abstract: A method for manufacturing a trench capacitor comprises the step of etching a shallow isolation trench in a two-step process flow. During the first etching step, an etch chemistry based on chlorine or bromine performs a highly selective etch for silicon (12). During the second step, the etch chemistry is based on SiF₄ and O₂ which rather equally etches polysilicon (12) and the collar isolation (22, 31). On top of the wafer, the deposition of silicon oxide on the hard mask (40) predominates and avoids an erosion of the hard mask (40). On the bottom (52) of the trench (50) the conformal etching of polysilicon (12) and collar isolation (22, 31) predominates. The method provides an economic process flow and is suitable for small feature sizes.

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